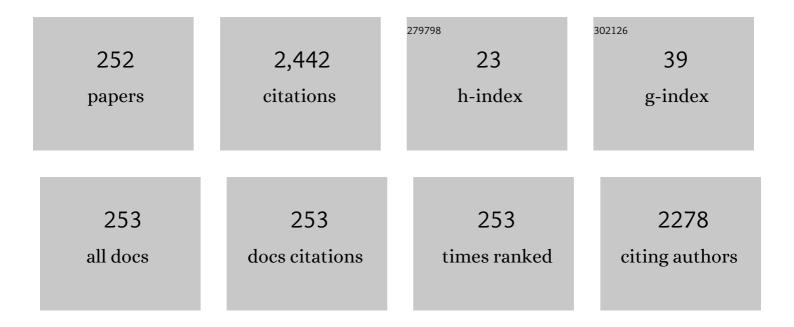
Naoki Wakiya

List of Publications by Year in descending order

Source: https://exaly.com/author-pdf/5435644/publications.pdf Version: 2024-02-01



NAOKI WAKIYA

#	Article	IF	CITATIONS
1	Band-gap energies of sol-gel-derived SrTiO3 thin films. Applied Physics Letters, 2001, 79, 3767-3769.	3.3	181
2	Synthesis and dielectric properties of Ba1â^'xR2x/3Nb2O6 (R: rare earth) with tetragonal tungsten bronze structure. Journal of the European Ceramic Society, 1999, 19, 1071-1075.	5.7	147
3	An XPS study of the nucleation and growth behavior of an epitaxial Pb(Zr,Ti)O3/MgO(100) thin film prepared by MOCVD. Thin Solid Films, 2000, 372, 156-162.	1.8	69
4	Estimation of Phase Stability in Pb(Mg _{1/3} Nb _{2/3})O ₃ and Pb(Zn _{1/3} Nb _{2/3})O ₃ Using the Bond Valence Approach. Journal of the American Ceramic Society, 1997, 80, 3217-3220.	3.8	66
5	Thermal stability of Pb(Zn13Nb23)O3 (PZN) and consideration of stabilization conditions of perovskite type compounds. Materials Research Bulletin, 1995, 30, 1121-1131.	5.2	57
6	Ferroelectric properties of sandwich structured (Bi, La)4T3O12/Pb(Zr, Ti)O3/ (Bi, La)4Ti3O12thin films on Pt/Ti/SiO2/Si substrates. Journal Physics D: Applied Physics, 2002, 35, L1-L5.	2.8	56
7	Investigations of superparamagnetism in magnesium ferrite nano-sphere synthesized by ultrasonic spray pyrolysis technique for hyperthermia application. Journal of Magnetism and Magnetic Materials, 2015, 392, 91-100.	2.3	55
8	Low-temperature epitaxial growth of conductive LaNiO3 thin films by RF magnetron sputtering. Thin Solid Films, 2002, 410, 114-120.	1.8	54
9	Synthesis and hyperthermia property of hydroxyapatite–ferrite hybrid particles by ultrasonic spray pyrolysis. Journal of Magnetism and Magnetic Materials, 2011, 323, 965-969.	2.3	53
10	Structural and electrical characteristics of chemical-solution-derived (Bi,La)4Ti3O12 thin films with various Bi2O3 template layers. Journal of Applied Physics, 2003, 93, 497-503.	2.5	48
11	Improved electrical properties of (Pb, La)TiO3 thin films using compositionally and structurally compatible LaNiO3 thin films as bottom electrodes. Applied Physics Letters, 2001, 78, 3286-3288.	3.3	47
12	Preparation of hydroxyapatite–ferrite composite particles by ultrasonic spray pyrolysis. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2010, 173, 195-198.	3.5	42
13	Stress-induced magnetization for epitaxial spinel ferrite filmsthrough interface engineering. Applied Physics Letters, 2004, 85, 1199-1201.	3.3	39
14	Structural, dielectric, and ferroelectric properties of PbTiO3 thin films by a simple sol–gel technique. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2002, 94, 269-274.	3.5	37
15	Abnormal ferroelectric properties of compositionally graded Pb(Zr,Ti)O3 thin films with LaNiO3 bottom electrodes. Journal of Applied Physics, 2001, 90, 506-508.	2.5	36
16	Epitaxial growth of SrTiO3 films on CeO2/yttria-stabilized zirconia/Si(001) with TiO2 atomic layer by pulsed-laser deposition. Applied Physics Letters, 2003, 83, 4815-4817.	3.3	36
17	Nucleation and growth behavior of epitaxial Pb(Zr,Ti)O 3 /MgO(100) observed by atomic force microscopy. Thin Solid Films, 1999, 357, 166-172.	1.8	30
18	Heteroepitaxial growth of CeO2 thin film on Si(001) with an ultra thin YSZ buffer layer. Thin Solid Films, 2000, 371, 211-217.	1.8	30

#	Article	IF	CITATIONS
19	Preparation of conductive LaNiO3film electrodes by a simple chemical solution deposition technique for integrated ferroelectric thin film devices. Journal Physics D: Applied Physics, 2003, 36, 1217-1221.	2.8	30
20	Phase Diagram and Microstructure in the ZnO–Pr ₂ O ₃ System. Journal of the American Ceramic Society, 1997, 80, 995-998.	3.8	27
21	Stress engineering of the alkoxide derived ferroelectric thin film on Si wafer. Journal of the Ceramic Society of Japan, 2009, 117, 1089-1094.	1.1	27
22	Superparamagnetic magnesium ferrite/silica core-shell nanospheres: A controllable SiO2 coating process for potential magnetic hyperthermia application. Advanced Powder Technology, 2019, 30, 3171-3181.	4.1	25
23	Impact of thin SrTiO3 seed layer to achieve low-temperature crystallization below 300°C and ferroelectricity of lead zirconate titanate thin film. Applied Physics Letters, 2006, 89, 202907.	3.3	24
24	Oxygen Sensing Properties of SrTiO3Thin Films. Japanese Journal of Applied Physics, 2008, 47, 7486-7489.	1.5	23
25	Effect of Liquid Phase and Vaporization on the Formation of Microstructure of Pr Doped ZnO Varistor. , 1999, 4, 15-23.		21
26	Raman Spectroscopic Determination of Pyrochlore-Type Compound on the Synthesis and Decomposition of Sol-Gel-Derived Pb(Mg1/3Nb2/3)O3(PMN). Journal of Solid State Chemistry, 1999, 142, 344-348.	2.9	21
27	Effect of the Thickness of SiO2 under Layer on the Initial Stage of Epitaxial Growth Process of Yttria-Stabilized Zirconia (YSZ) Thin Film Deposited on Si(001) Substrate Journal of the Ceramic Society of Japan, 2001, 109, 766-770.	1.3	21
28	Preparation of heteroepitaxial Pb(Mg1/3Nb2/3)O3 (PMN) thin film by pulsed laser deposition on Si(001) substrate using La0.5Sr0.5CoO3 (LSCO)/CeO2/YSZ triple buffer. Thin Solid Films, 2001, 384, 189-194.	1.8	21
29	Growth of highly (001)-textured strontium barium niobate thin films on epitaxial LaNiO3/CeO2/YSZ/Si(100). Thin Solid Films, 2003, 426, 62-67.	1.8	21
30	Effect of Oxygen Annealing on Ferroelectricity of BiFeO3Thin Films Formed by Pulsed Laser Deposition. Japanese Journal of Applied Physics, 2007, 46, 3491-3494.	1.5	21
31	Impact of acidic catalyst to coat superparamagnetic magnesium ferrite nanoparticles with silica shell via sol–gel approach. Advanced Powder Technology, 2016, 27, 541-549.	4.1	20
32	RF-magnetron-sputtered heteroepitaxial YSZ and CeO2/YSZ/Si(001) thin films with improved capacitance–voltage characteristics. Thin Solid Films, 2002, 411, 268-273.	1.8	19
33	Electrooptic Properties of Epitaxial Lead Zirconate Titanate Films on Silicon Substrates. Japanese Journal of Applied Physics, 2007, 46, 6929.	1.5	19
34	Effect of Film Thickness on Electrical Properties of Chemical Solution Deposition-Derived Pb(ZrxTi1-x)O3/LaNiO3/Si. Japanese Journal of Applied Physics, 2007, 46, 6925-6928.	1.5	19
35	Modification of Ferroelectric Properties of BaTiO3–CoFe2O4Multiferroic Composite Thin Film by Application of Magnetic Field. Japanese Journal of Applied Physics, 2008, 47, 7603-7606.	1.5	19
36	Magnetic-field-induced spontaneous superlattice formation via spinodal decomposition in epitaxial strontium titanate thin films. NPG Asia Materials, 2016, 8, e279-e279.	7.9	19

#	Article	IF	CITATIONS
37	Oxygen sensitivity of perovskite-type dielectric thin films. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2009, 161, 142-145.	3.5	18
38	Phase diagram and piezoelectric response of (Ba _{1â^'<i>x</i>} Ca _{<i>x</i>})(Zr _{0.1} Ti _{0.9})O ₃ solid solution. Journal of Physics Condensed Matter, 2013, 25, 425901.	1.8	18
39	Influence of crystallite size on the magnetic and heat generation properties of La0.77Sr0.23MnO3 nanoparticles for hyperthermia applications. Journal of Physics and Chemistry of Solids, 2018, 112, 179-184.	4.0	18
40	Composition Range of Cubic Pyrochlore Type Compound in Lead-Magnesium-Niobium-Oxygen System. Journal of the Ceramic Society of Japan, 1994, 102, 612-615.	1.3	17
41	Stress Control and Ferroelectric Properties of Lead Zirconate Titanate (PZT) Thin Film on Si Substrate with Buffer Layers. Japanese Journal of Applied Physics, 2005, 44, 6900-6904.	1.5	17
42	Valence-EELS analysis of local electronic and optical properties of PMN–PT epitaxial film. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2009, 161, 160-165.	3.5	17
43	Low-temperature processing of Garnet-type ion conductive cubic Li7La3Zr2O12 powders for high performance all solid-type Li-ion batteries. Journal of the Taiwan Institute of Chemical Engineers, 2018, 90, 85-91.	5.3	17
44	Effect of Yttria-Stabilized Zirconia Thickness on Crystal Structure and Electric Property of Epitaxial CeO2/Yttria-Stabilized Zirconia Buffer Layer in Metal/Ferroelectric/Insulator/Semiconductor Structure. Japanese Journal of Applied Physics, 2001, 40, 281-284.	1.5	16
45	Impact of precursor solution concentration to form superparamagnetic MgFe2O4 nanospheres by ultrasonic spray pyrolysis technique for magnetic thermotherapy. Advanced Powder Technology, 2017, 28, 1696-1703.	4.1	16
46	Controlled synthesis of dense MgFe2O4 nanospheres by ultrasonic spray pyrolysis technique: Effect of ethanol addition to precursor solvent. Advanced Powder Technology, 2018, 29, 283-288.	4.1	16
47	Influence of ultra-thin YSZ layer on heteroepitaxial CeO2/YSZ/Si(001) films analyzed by X-ray reciprocal space map. Journal of Crystal Growth, 2000, 219, 253-262.	1.5	15
48	Fabrication and optical properties of Pb(Mg _{1/3} Nb _{2/3})O ₃ -PbTiO ₃ thin films on Si substrates using the PLD method. IEEE Transactions on Ultrasonics, Ferroelectrics, and Frequency Control, 2008, 55, 1023-1028.	3.0	15
49	Progress and impact of magnetic field application during pulsed laser deposition (PLD) on ceramic thin films. Journal of the Ceramic Society of Japan, 2017, 125, 856-865.	1.1	15
50	Charge screening strategy for domain pattern control in nano-scale ferroelectric systems. Scientific Reports, 2017, 7, 5236.	3.3	14
51	Origin of Compressive Residual Stress in Alkoxide Derived PbTiO3Thin Film on Si Wafer. Japanese Journal of Applied Physics, 2008, 47, 7514-7518.	1.5	13
52	Effect of the electrode structure on the electrical properties of alkoxide derived ferroelectric thin film. Materials Letters, 2010, 64, 1742-1744.	2.6	13
53	Magnetic and photocatalytic properties of n- and p-type ZnFe ₂ 0 ₄ particles synthesized using ultrasonic spray pyrolysis. Journal of the Ceramic Society of Japan, 2013, 121, 26-30.	1.1	13
54	As-grown enhancement of spinodal decomposition in spinel cobalt ferrite thin films by Dynamic Aurora pulsed laser deposition. Journal of Magnetism and Magnetic Materials, 2017, 432, 391-395.	2.3	13

#	Article	IF	CITATIONS
55	Stabilization of perovskite Pb(Mg1/3Nb2/3)O3 thin film by a thin BaTiO3 buffer layer on Pt/Ti/SiO2/Si. Thin Solid Films, 2002, 409, 248-253.	1.8	12
56	Low-temperature crystallization of CSD-derived PZT thin film with laser assisted annealing. Journal of the Ceramic Society of Japan, 2009, 117, 950-953.	1.1	12
57	Low-temperature crystallization of CSD-derived PZT thin film with laser annealing. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2010, 173, 89-93.	3.5	12
58	Fabrication of 12CaO 7Al2O3 powders with high specific surface area by sol-gel and ball-milling method. Journal of the Ceramic Society of Japan, 2011, 119, 460-463.	1.1	12
59	Effect of Stress Engineering on the Electrical Properties of BaTiO\$_{3}\$ Thin Film. Japanese Journal of Applied Physics, 2011, 50, 09NA03.	1.5	12
60	Effect of facing annealing on crystallization and decomposition of Pb(Mg _{1/3} Nb _{2/3})O ₃ thin films prepared by CSD technique using MOD solution. Journal of the Ceramic Society of Japan, 2013, 121, 236-241.	1.1	12
61	Effect of atmosphere on stability of Pb(Mg13Nb23)O3 (PMN) ceramics. Materials Research Bulletin, 1997, 32, 451-459.	5.2	11
62	Influence of atmosphere on phase transitions of praseodymium oxide at high temperature using high temperature X-ray diffraction and thermogravimetry. Thermochimica Acta, 1998, 313, 55-61.	2.7	11
63	Preparation and Characterization of Alkoxide-Derived Lead-Free Piezoelectric Barium Zirconate Titanate Thin Films with Different Compositions. Japanese Journal of Applied Physics, 2010, 49, 09MA11.	1.5	11
64	Magnetic-field-induced phase separation via spinodal decomposition in epitaxial manganese ferrite thin films. Science and Technology of Advanced Materials, 2018, 19, 507-516.	6.1	11
65	Orientation Control and Properties of Pb(Zr, Ti)O3Thin Films Deposited on Ni–Zn-Ferrite for Novel Ferroelectric/Ferromagnetic Memory Applications. Japanese Journal of Applied Physics, 2002, 41, 7242-7248.	1.5	10
66	HRTEM investigation of the 90Ű domain structure and ferroelectric properties of multi-layered PZT thin films. Microelectronic Engineering, 2003, 66, 708-712.	2.4	10
67	Electrooptic Properties of Lead Zirconate Titanate Films Prepared on Silicon Substrate. Japanese Journal of Applied Physics, 2006, 45, 7516-7519.	1.5	10
68	Effects of synthesis conditions on electrical properties of chemical solution deposition-derived Pb(Mg1/3Nb2/3)O3–PbTiO3 thin films. Thin Solid Films, 2015, 585, 86-90.	1.8	10
69	Orientation control of SrRuO3 thin film on a Si substrate by chemical solution deposition for an electrode of lead zirconate titanate thin films. Materials Letters, 2016, 181, 74-77.	2.6	10
70	Synthesis of a new compound, Ca0.8Ce1.2Sn2O7, with pyrochlore structure. Journal of Solid State Chemistry, 1991, 92, 320-326.	2.9	9
71	Effect of the Sintering Temperature and Atmosphere on the Grain Growth and Grain Boundary Phase Formation of Pr-Doped ZnO Varistor. Journal of the Ceramic Society of Japan, 1996, 104, 44-48.	1.3	9
72	Preparation and Properties of Novel Ferroelectric and Ferromagnetic Array Structure Thin Film. Ferroelectrics, 2002, 273, 149-154.	0.6	9

#	Article	IF	CITATIONS
73	Fabrication of transition temperature controlled W-doped VO2 nano particles by aqueous solution. Journal of the Ceramic Society of Japan, 2011, 119, 522-524.	1.1	9
74	Effect of Thermal Stress on Orientation Control of <scp>CSD</scp> â€Derived <scp><scp>Pb(Zr_{0.53}Ti_{0.47})O₃</scp></scp> Thin Films. International Journal of Applied Ceramic Technology, 2012, 9, 868-875.	2.1	9
75	Effect of the reduction condition on the catalytic activity for steam reforming process using Ni doped LaAlO 3 nano-particles. Advanced Powder Technology, 2016, 27, 179-183.	4.1	9
76	Synthesis and electrical properties of Pb(Mg1/3Nb2/3)O3–PbTiO3 epitaxial thin films on Si wafers using chemical solution deposition. Thin Solid Films, 2016, 603, 97-102.	1.8	9
77	Measurement Technique for the Evaluation of Residual Stress in Epitaxial Thin Film by Asymmetric X-Ray Diffraction Journal of the Ceramic Society of Japan, 1999, 107, 606-610.	1.3	8
78	Growth Mechanism of SrTiO ₃ Thin Film on CeO ₂ (001) Surface. Key Engineering Materials, 2002, 228-229, 137-140.	0.4	8
79	Effects of thermal coefficient and lattice constant mismatches on mosaic dispersion of heteroepitaxial YSZ/Si(001) thin films. Journal Physics D: Applied Physics, 2002, 35, 151-156.	2.8	8
80	Improvement of Magnetic Properties of (111)-Epitaxial Nickel-Zinc-Ferrite Thin Films Deposited on Si Platform. Key Engineering Materials, 2004, 269, 245-0.	0.4	8
81	Thermochromic tungsten doped VO2-SiO2 nano-particle synthesized by chemical solution deposition technique. Journal of the Ceramic Society of Japan, 2009, 117, 970-972.	1.1	8
82	Molecular design effects of alkoxide-derived precursor solution on low-temperature crystallization of cubic garnet type Li ion conductor. Materials Letters, 2021, 283, 128747.	2.6	8
83	Formation conditions for a pyrochlore structure with two different cations at the A site. Journal of Solid State Chemistry, 1992, 101, 71-76.	2.9	7
84	Phase Transformation and Densification Behavior of La-Modified Lead Metaniobate Ceramics Journal of the Ceramic Society of Japan, 2001, 109, 89-93.	1.3	7
85	Special Issue Ceramics Integration. Role of Ultra Thin SiOx Layer for Epitaxial Growth of YSZ/SiOx/(001)Si Thin Films Journal of the Ceramic Society of Japan, 2002, 110, 338-342.	1.3	7
86	Role of Ultra Thin SiOx Layer on Epitaxial YSZ/SiOx/Si Thin Film. Integrated Ferroelectrics, 2003, 51, 51-61.	0.7	7
87	Preparation and Structure of Lead Magnesium Niobate Titanate Film by Double-Pulse Excitation using Nd:YAG and KrF Excimer Lasers. Japanese Journal of Applied Physics, 2007, 46, 657-659.	1.5	7
88	Advantage of the structure and the electrical properties of epitaxial ultra-thin zirconia gate dielectrics. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2008, 148, 30-34.	3.5	7
89	Effect of SrTiO3 seed layer deposition time and thickness on low-temperature crystallization and electrical properties of Pb(Zr, Ti)O3 films by metalorganic chemical vapor deposition. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2008, 148, 22-25.	3.5	7
90	Preparation of MgIn2O4Epitaxial Oxide Electrode with Spinel Structure and Heteroepitaxial Growth of BaTiO3–NiFe2O4Multiferroic Composite Thin Film. Japanese Journal of Applied Physics, 2009, 48, 09KB06.	1.5	7

#	Article	IF	CITATIONS
91	Effect of bottom electrode structure on electrical properties of BaTiO3 thin films fabricated by CSD method. Journal of the Ceramic Society of Japan, 2010, 118, 669-673.	1.1	7
92	Thermal radiative properties of (La1â^xSrx)MnO3â^î^t thin films fabricated on yttria-stabilized zirconia single-crystal substrate by pulsed laser deposition. Thin Solid Films, 2015, 593, 1-4.	1.8	7
93	Magnetic and Mechanical Properties of Iron-Based Soft Magnetic Composites Coated with Silane Synergized by Bi2O3. Journal of Electronic Materials, 2021, 50, 2425-2435.	2.2	7
94	Structural and Ferroelectric Properties of (1-X)Ba3.75Y0.83Nb10O30-XBa3.75Sm0.83Nb10O30 Solid Solutions Journal of the Ceramic Society of Japan, 2000, 108, 36-39.	1.3	6
95	Redox Reaction of Praseodymium Oxide in the ZnO Sintered Ceramics. Journal of Solid State Chemistry, 2000, 149, 349-353.	2.9	6
96	Special Issue Ceramics Integration. Change of Residual Stresses and Electrical Properties of Pb(Zr,Ti)O3 Thin Films Upon Introducing Various Bottom Electrodes Journal of the Ceramic Society of Japan, 2002, 110, 421-427.	1.3	6
97	Improvement of C-V Characteristics and Control of Interlayer Growth of Rare Earth Oxide Stabilized Zirconia Epitaxial Gate Dielectrics. Key Engineering Materials, 2003, 248, 137-142.	0.4	6
98	Activation Energy of Oxygen Vacancy Diffusion of Yttria-Stabilized-Zirconia Thin Film Determined from DC Current Measurements below 150 °C. Japanese Journal of Applied Physics, 2006, 45, L525-L528.	1.5	6
99	Preparation and Optical Properties of Epitaxial Pb(Mg _{1/3} Nb _{2/3})O ₃ -PbTiO _{3< Thin Film on Si Substrates with Buffer Layer Using Pulsed Laser Deposition. Key Engineering Materials, 2006, 301, 265-268.}	/sub> 0.4	6
100	Fabrication and Microstructural Change of PMN-PT Thin Films on Si Substrates by PLD with Mask and Double-Pulse Lazer Excitation. Key Engineering Materials, 2007, 350, 111-114.	0.4	6
101	Spray Pyrolysis of Fe3O4-BaTiO3Composite Particles. Journal of the American Ceramic Society, 2009, 92, S177-S180.	3.8	6
102	Solution derived 12CaO·7Al2O3 thin films on MgO(100) substrate. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2010, 173, 21-24.	3.5	6
103	Magnetic field effects during deposition on crystal structure and magnetic properties of BaFe ₁₂ O ₁₉ thin films prepared using PLD in the magnetic field (Dynamic aurora PLD). Journal of the Ceramic Society of Japan, 2013, 121, 45-48.	1.1	6
104	Stress engineering for the design of morphotropic phase boundary in piezoelectric material. Thin Solid Films, 2015, 585, 91-94.	1.8	6
105	Preparation of (La1â^'xSrx)MnO3â^'δ thin films on Si (100) substrates by a metal-organic decomposition method for smart radiation devices. Thin Solid Films, 2017, 626, 154-158.	1.8	6
106	<i>I-V</i> Characteristics of Single Grain Boundary in ZnO Varistor. Journal of the Ceramic Society of Japan, 1991, 99, 788-792.	1.3	5
107	Electrical Conduction of New Compounds (Ca, Ce)2Sn2O7 and (Sr, Ce)2Sn2O7 with Pyrochlore Structure. Journal of Solid State Chemistry, 1993, 102, 349-353.	2.9	5
108	Investigation of the solidus boundaries and microstructure in the ZnO–PrO1.5–CoO system. Journal of Materials Research, 1998, 13, 2110-2116.	2.6	5

#	Article	IF	CITATIONS
109	Proposal and preparation of novel fluorite/spinel heteroepitaxial double buffer layer structure on Si(001) for FET-type fram application. Ferroelectrics, 2001, 259, 277-282.	0.6	5
110	Special Issue Ceramics Integration. Electrical Properties of Epitaxial La0.5Sr0.5CoO3(LSCO) Thin Films Prepared in Low Oxygen Pressure Journal of the Ceramic Society of Japan, 2002, 110, 353-357.	1.3	5
111	Modification of drain current on metal–oxide–semiconductor field-effect transistor by magnetic field induced by remanent magnetization. Applied Physics Letters, 2004, 85, 3772-3774.	3.3	5
112	High-temperature in situ Cross-sectional Transmission Electron Microscopy Investigation of Crystallization Process of Yttrium-stabilized Zirconia/Si and Yttrium-stabilized Zirconia/SiOx/Si Thin Films. Journal of Materials Research, 2005, 20, 1878-1887.	2.6	5
113	Oxygenâ€Enhanced Crystallization of Solutionâ€Derived 12CaO·7Al ₂ O ₃ . Journal of the American Ceramic Society, 2009, 92, S189.	3.8	5
114	Magnetic and optical properties of MgAl2O4-(Ni0.5Zn0.5)Fe2O4thin films prepared by pulsed laser deposition. Science and Technology of Advanced Materials, 2011, 12, 034408.	6.1	5
115	Magnetic Properties of Epitaxial NiFe ₂ O ₄ Thin Films Prepared Using Dynamic Aurora PLD in a Magnetic Field. Key Engineering Materials, 2011, 485, 221-224.	0.4	5
116	Strain-Induced Electrical Properties of Lead Zirconate Titanate Thin Films on a Si wafer with Controlled Oxide Electrode Structure. Japanese Journal of Applied Physics, 2012, 51, 09LA13.	1.5	5
117	Structure Analysis of CeO2/ZrO2/Si Multilayer Thin Films by HRTEM. Materials Research Society Symposia Proceedings, 1999, 592, 191.	0.1	4
118	Effect of the Residual Stress Induced by External Stress Application on Dielectric Properties of Epitaxial Lead Titanate Film Journal of the Ceramic Society of Japan, 2000, 108, 21-25.	1.3	4
119	Effects of Nb and Sr doping on crystal structure of epitaxial BaTiO3 thin films on MgO substrates. Journal Physics D: Applied Physics, 2002, 35, 1499-1503.	2.8	4
120	Special Issue Ceramics Integration. Preparation of Epitaxial YSZ Thin Film Deposited on SiO2/Si(001) at Room Temperature by Pulsed Laser Deposition(PLD) Journal of the Ceramic Society of Japan, 2002, 110, 333-337.	1.3	4
121	Growth Behavior of Epitaxial MgO Films on Si(001) by Pulsed Laser Deposition. Key Engineering Materials, 2003, 253, 119-128.	0.4	4
122	Preparation of Epitaxial LiTaO ₃ Thin Films by Metal Organic Chemical Vapor Deposition and its Electrical and Optical Properties. Key Engineering Materials, 2006, 320, 57-60.	0.4	4
123	Preparation of Epitaxial LiNbO ₃ Thin Film by MOCVD and its Properties. Key Engineering Materials, 0, 388, 179-182.	0.4	4
124	Shape controlled ZnO nanoparticle prepared by microwave irradiation method. Journal of the Ceramic Society of Japan, 2009, 117, 961-963.	1.1	4
125	Microstructure and electrical properties of BaTiO3 thin films by modified CSD. Journal of the Ceramic Society of Japan, 2011, 119, 498-501.	1.1	4
126	Micro/Crystal structure analysis of CSD derived porous LaNiO ₃ electrode films. Journal of the Ceramic Society of Japan, 2013, 121, 619-622.	1.1	4

#	Article	IF	CITATIONS
127	Catalytic Activity for the Methane Steam Reforming Process Using Chemical Solution Deposition Derived Barium Titanate Hollow Particles with Perovskite Mono-phase. Journal of the Society of Powder Technology, Japan, 2014, 51, 337-342.	0.1	4
128	Interface structure of Pb(Zr,Ti)O3/MgO(001) epitaxial thin film in early stage of Stranski–Krastanov growth mode. Japanese Journal of Applied Physics, 2019, 58, SLLA08.	1.5	4
129	Properties of MgFe2O4 Nanoparticles Synthesized by Ultrasonic Aerosol Pyrolysis for Biomedical Applications. Physics of the Solid State, 2019, 61, 1113-1121.	0.6	4
130	Enhanced Magnetoelectric Effects in Self-Assembled Hemispherical Close-Packed CoFe2O3-Pb(Zr0.52Ti0.48)O3 Thin Film. Journal of Electronic Materials, 2021, 50, 1699-1706.	2.2	4
131	Relationship between the Evaporation of Components and Microstructure in Pr-Doped ZnO Ceramics. Journal of the Ceramic Society of Japan, 1996, 104, 1056-1059.	1.3	3
132	Effect of A Site Substitution on Order-Disorder Transition in Pb(Fe _{1/2} Nb _{1/2})O ₃ (PFN) and Pb(Sc _{1/2} Ta _{1/2})O ₃ (PST). Journal of the Ceramic Society of Japan, 1996, 104, 691-694.	1.3	3
133	Preparation of Homo and Hetero Multilayer YSZ Thin Films by Ultrasonic Spray ICP Flash Evaporation Method. Journal of the Ceramic Society of Japan, 1998, 106, 312-316.	1.3	3
134	Morphotropic Phase Boundary (MPB) of Tungsten Bronze Type New Compounds (Pb1-xLa2x/3)5Nb10O30 (X=0.0-0.50) Journal of the Ceramic Society of Japan, 2000, 108, 785-789.	1.3	3
135	Preparation of epitaxial YSZ thin film on Si(001) using metal and oxide targets by RF-magnetron sputtering. Ferroelectrics, 2001, 260, 249-254.	0.6	3
136	Effects of deposition temperature on structural defect and electrical resistivity in heteroepitaxial La0.5Sr0.5CoO3/CeO2/YSZ/Si films. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2002, 20, 1749-1754.	2.1	3
137	Film Thickness Dependence of Structural and Dielectric Properties of Pb(Mg _{1/3} Nb _{2/3})O ₃ /BaTiO ₃ /Pt/Ti/SiO ₂ /Si. Key Engineering Materials, 2002, 228-229, 87-92.	0.4	3
138	Special Issue Ceramics Integration. Effect of Composition and Crystallinity of Epitaxial Ni-Zn Ferrite Films by Pulsed Laser Deposition on their Magnetic Properties Journal of the Ceramic Society of Japan, 2002, 110, 428-431.	1.3	3
139	Hrteminvestigation of 90° Domain Configureuration and P-E Hysteresis Loop of Epitaxial PZT Multilayered Thin Films. Materials Research Society Symposia Proceedings, 2002, 748, 1.	0.1	3
140	Special Issue Ceramics Integration. Crystal Growth of Pb(Zr,Ti)O3(PZT) Thin Film by Introducing SrTiO3 Seed Buffer Layer Journal of the Ceramic Society of Japan, 2002, 110, 358-361.	1.3	3
141	Special Issue Ceramics Integration. Controlling Crystallinity and Crystal Oritentation of PbTiO3 and Pb(Zr,Ti)O3 Thin Films by Introducing Different Seed Layers Journal of the Ceramic Society of Japan, 2002, 110, 362-367.	1.3	3
142	Effective Buffer Structures and Dielectric Properties of Epitaxial Pb(Mg _{1/3} Nb _{2/3})O ₃ Thin Films on Si Substrates. Key Engineering Materials, 2003, 248, 65-68.	0.4	3
143	AEM Investigation of Interface Structure of Y ₂ O ₃ -Ta ₂ O ₅ Co-Doped Zirconia Buffer Layer. Key Engineering Materials, 2004, 269, 237-240.	0.4	3
144	Effect of Substrate Size on Crystalline Orientation and Electrical Properties of (Bi, La)4Ti3O12 Thin Films. Journal of the Ceramic Society of Japan, 2004, 112, 266-270.	1.3	3

#	Article	IF	CITATIONS
145	Effect of Source Supply Methods on Low-Temperature Preparation of Lead Zirconate Titanate Thin Films Using SrTiO ₃ Seed Layers by Metallorganic Chemical Vapor Deposition. Solid State Phenomena, 2007, 124-126, 153-156.	0.3	3
146	Low-Frequency Raman Spectroscopy in Pb(Zn _{1/3} Nb _{2/3})O ₃ -PbTiO ₃ Mixed Crystals. Ferroelectrics, 2009, 378, 84-91.	0.6	3
147	Doping effect of Dy on leakage current and oxygen sensing property of SrTiO3 thin film prepared by PLD. Journal of the Ceramic Society of Japan, 2009, 117, 1004-1008.	1.1	3
148	Enhanced electrical properties of ferroelectric thin films with electric field induced domain control. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2010, 173, 25-28.	3.5	3
149	Characterization of Low Temperature Chemical Vapor Deposited Gd ₂ 0 ₃ Doped CeO ₂ Films. Key Engineering Materials, 0, 485, 133-136.	0.4	3
150	Fabrication of two-dimensional close-packed shell structure in ceramic thin films. Science and Technology of Advanced Materials, 2011, 12, 034405.	6.1	3
151	TEM MICROSTRUCTURE ANALYSIS FOR COMPRESSIVELY STRESSED Pb(Zr,Ti)O₃ THIN FILMS BY CSD-DERIVED LaNiO₃ BOTTOM ELECTRODES. Functional Materials Letters, 2012, 05, 1260016.	1.2	3
152	Low temperature processing of alkoxide-derived PMN thin films. IOP Conference Series: Materials Science and Engineering, 2012, 30, 012002.	0.6	3
153	Preparation of free-standing multilayer hemispherical shell thin film using monodisperse polymer template. Journal of Alloys and Compounds, 2018, 730, 369-375.	5.5	3
154	Effect of Stress Engineering on the Electrical Properties of BaTiO3Thin Film. Japanese Journal of Applied Physics, 2011, 50, 09NA03.	1.5	3
155	Strain-Induced Electrical Properties of Lead Zirconate Titanate Thin Films on a Si wafer with Controlled Oxide Electrode Structure. Japanese Journal of Applied Physics, 2012, 51, 09LA13.	1.5	3
156	Crystal Structural Studies of Thermal Decomposition Process of PbMg _{1/3} Nb _{2/3} O ₃ Single Crystal into Pyrochlore Type Compound. Journal of the Ceramic Society of Japan, 1994, 102, 8-12.	1.3	2
157	Preparation of NdBa2Cu3Oy thin films by mist ICP evaporation. Thin Solid Films, 1998, 334, 87-91.	1.8	2
158	Preparation of PbTiO3Thin Film by Mist Source Plasma Enhanced Chemical Vapor Deposition (CVD) Using Heptane Solvent. Japanese Journal of Applied Physics, 1999, 38, 5326-5331.	1.5	2
159	Structural Study of PbZn1/3Nb2/3O3 by Single Crystal X-ray Diffraction and EXAFS Journal of the Ceramic Society of Japan, 2000, 108, 617-622.	1.3	2
160	Defects in heteroepitaxial CeO2/YSZ/Si(001) films by precise X-ray rocking curve distribution fitness. Physica B: Condensed Matter, 2001, 308-310, 1050-1053.	2.7	2
161	Analysis of Formation Process of Ferroelectric Domain Structure in PZT Thin Films by In-Situ TEM. Key Engineering Materials, 2002, 228-229, 203-206.	0.4	2
162	Orientation Control and Domain Structure of Epitaxial (Ni,Zn)Fe ₂ 0 ₄ Thin Film for Ferromagnetic Memory Applications. Key Engineering Materials, 2003, 248, 169-172.	0.4	2

#	Article	IF	CITATIONS
163	Proposal of general rule to prepare epitaxial ceramic thin films at low temperature from the point of crystal chemistry. Ceramics International, 2004, 30, 1247-1251.	4.8	2
164	Room-Temperature Electrical-Field Induced Oxygen Diffusion of Aluminum/Yttria-Stabilized Zirconia Thin Film Grown on Si Substrate. Japanese Journal of Applied Physics, 2006, 45, 8827-8831.	1.5	2
165	Effect of Back-Etching on Electrical Properties of (001)&(100) Oriented PZT(30/70) Thin Films. Ferroelectrics, 2008, 370, 119-125.	0.6	2
166	Nanostructure and strain analysis of CeO2/YSZ strained superlattice. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2010, 173, 220-228.	3.5	2
167	Effect of Substrate on Growth Mechanism of Flower Structured InN Fabricated by APHCVD. Key Engineering Materials, 0, 445, 209-212.	0.4	2
168	Fabrication of Vanadium Dioxide Nano-particles by Microemulsion Method with Controlled Phase Transition Temperatures. Funtai Oyobi Fummatsu Yakin/Journal of the Japan Society of Powder and Powder Metallurgy, 2014, 61, 99-103.	0.2	2
169	Low temperature and fast growth of one-directionally grown aluminum nitride film by atmospheric pressure halide CVD method. Journal of the Ceramic Society of Japan, 2019, 127, 612-616.	1.1	2
170	Magnetoelectric Studies of Close-Packed and Hierarchically Ordered CoFe2O4/Pb(Zr0.52Ti0.48)O3/La0.6Sr0.4MnO3/LaNiO3 Multiferroic Thin Films. Journal of Electronic Materials, 2021, 50, 1678-1685.	2.2	2
171	Spontaneous superlattice formation and electrical properties of Sr-excess SrTiO ₃ thin film deposited on SrTiO ₃ (101) by dynamic aurora pulsed laser deposition. Journal of the Ceramic Society of Japan, 2021, 129, 390-396.	1.1	2
172	Dynamic Aurora PLD with Si and porous Si to prepare ZnFe ₂ 0 ₄ Thin films for liquefied petroleum gas sensing. Journal of the Ceramic Society of Japan, 2020, 128, 457-463.	1.1	2
173	Preparation and characterization of epitaxially grown yttria-stabilized zirconia thin films on porous silicon substrates for solid oxide fuel cell applications. Journal of the Ceramic Society of Japan, 2022, 130, 464-470.	1.1	2
174	Effect of Ionic Radii on Formation and Properties of (M ²⁺ _{1-x} Ln ³⁺ _{2x/3}) ₅ Nb ₁₀ O _{3 (M=Sr,Pb,Ba, Ln=Rare Earth) New Ferroelectric Compounds Having Tungsten Bronze Structure. Key Engineering Materials, 2000, 181-182, 31-34.}	0.4 0.4	1
175	Preparation and Magnetic Properties of Heteroepitaxial NiFe ₂ O ₄ /(MgO-Al ₂ O ₃)/CeO ₂ /YSZ/Si(001) Thin Film. Key Engineering Materials, 2001, 214-215, 171-176.	0.4	1
176	Conduction Mechanism of La-, Nb-Doped BaTiO ₃ Thin Films by Doping MOCVD. Key Engineering Materials, 2001, 216, 87-92.	0.4	1
177	Role of Ultra Thin SiOx Layer on Epitaxial YSZ/SiOx/Si Thin Film as Multi Functional Buffer Layer by Nano-Probe and In-Situ TEM Investigation. Integrated Ferroelectrics, 2002, 45, 89-96.	0.7	1
178	Preparation and Properties of Novel Heteroepitaxial Metal/Ferroelectric/Metal/Insulator/Semiconductor (MFMIS) Structure for Pt/Pb(Zr,Ti)O3/(La,Sr)CoO3/SrTiO3/(Ni,Zn,Fe)Fe2O4/(MgO-Al2O3)/CeO2/YSZ/Si Thin Films. Key Engineering Materials, 2002, 228-229, 75-80.	0.4	1
179	Preparation of Tungsten Bronze Type Ferroelectric Ba _{0.75} Y _{0.166} Nb ₂ O _{6Thin Films by RF Magnetron Sputtering with LaNiO₃ Bottom Electrodes. Key Engineering Materials. 2002. 228-229. 99-106.}	t: 0.4	1
180	Role of the First Atomic Layers in Epitaxial Relationship and Interface Characteristics of SrTiO3 Films on CeO2/YSZ/Si(001). Materials Research Society Symposia Proceedings, 2002, 747, 1.	0.1	1

#	Article	IF	CITATIONS
181	Special Issue Ceramics Integration. Effects of Ambient Gas and Film Thickness on Orientation and Surface Morphology of Sr0.5Ba0.5Nb2O6 Thin Films Prepared by Pulsed Laser Deposition Journal of the Ceramic Society of Japan, 2002, 110, 368-372.	1.3	1
182	Special Issue Ceramics Integration. Growth Behavior of Bi and Nb Co-Added-SrTiO3 Thin Film Exhibiting Varistor Characteristics by Metal-Organic Chemical Vapor Deposition Journal of the Ceramic Society of Japan, 2002, 110, 416-420.	1.3	1
183	Orientation Control of Bi-La-Ti-O Thin Films Derived by Chemical Solution Deposition Method. Key Engineering Materials, 2003, 248, 49-52.	0.4	1
184	Effect of Source Supply Method on Microstructure Development in PZT Thin Films by Pulsed Metalorganic Chemical Vapor Deposition. Key Engineering Materials, 2003, 248, 53-56.	0.4	1
185	Control of Crystal Orientations and Its Electrical Properties of PZT/Ru and PZT/RuO2 Thin Films by MOCVD. Materials Research Society Symposia Proceedings, 2003, 768, 381.	0.1	1
186	Dielectric Properties and its Frequency Dependence of BaTiO ₃ Thin Film Single-Layer Capacitor that is Applicable to Multilayer Structure. Key Engineering Materials, 2004, 269, 229-232.	0.4	1
187	IN-SITU TEM INVESTIGATION OF STRUCTURAL CHANGES IN ZIRCONIA/SILICON HETEROSTRUCTURES AT ELEVATED TEMPERATURE. International Journal of Nanoscience, 2004, 03, 699-705.	0.7	1
188	Effects of Heating Process on Crystalline Orientation and Electrical Properties of (Bi,La)4Ti3O12 Thin Films Derived by Chemical Solution Deposition Method. Integrated Ferroelectrics, 2004, 62, 189-192.	0.7	1
189	In Situ Simultaneous Observation of Phase Transition and Electrical Properties of Pb(Zr,Ti)O ₃ Thin Film by High Temperature XRD and Electrical Measurement Apparatus. Key Engineering Materials, 2006, 320, 53-56.	0.4	1
190	Effect on Crystal Orientation on Residual Stress and Electrical Properties of a PZT Thin Film Deposited on Buffered-Si Substrate. Key Engineering Materials, 2006, 320, 65-68.	0.4	1
191	Tunable Barium Strontium Titanate Thin Films by CSD. Key Engineering Materials, 0, 445, 156-159.	0.4	1
192	Ferroelectricity of SrTiO ₃ Thin Films Prepared by Dynamic-Aurora Pulsed Laser Deposition. Key Engineering Materials, 2011, 485, 11-14.	0.4	1
193	BaTiO₃ THIN FILM BY CSD FROM MOLECULAR-DESIGNED PRECURSOR SOLUTION. Functional Materials Letters, 2012, 05, 1260007.	1.2	1
194	Effect of step edges on the growth of Pt thin films on oxide single-crystal substrates. Journal of the Ceramic Society of Japan, 2013, 121, 278-282.	1.1	1
195	Low-temperature Synthesis of 12CaO • 7Al2O3 Particles by Solution Plasma Processing. Funtai Oyobi Fummatsu Yakin/Journal of the Japan Society of Powder and Powder Metallurgy, 2014, 61, 93-98.	0.2	1
196	Catalytic Activities of Alkoxide-derived LaAlO ₃ for Ethanol Steam Reforming Processing. Transactions of the Materials Research Society of Japan, 2015, 40, 51-54.	0.2	1
197	Preparation and Analysis of New Phase of Calcium Aluminate Prepared by Solution Plasma Processing. Journal of the Society of Powder Technology, Japan, 2017, 54, 4-9.	0.1	1
198	Effect of deposition conditions and buffer layers on amorphous or polytype phase formation in Al ₂ O ₃ thin films by chemical vapor deposition using tri-methyl aluminum. Journal of the Ceramic Society of Japan, 2019, 127, 443-450.	1.1	1

#	Article	IF	CITATIONS
199	Magnetoelectric effect in free-standing multiferroic thin film. Journal of Alloys and Compounds, 2019, 787, 1128-1135.	5.5	1
200	As-grown Mn ₃ CuN thin films with high crystallinity prepared by dynamic aurora pulsed laser deposition. Journal of the Ceramic Society of Japan, 2021, 129, 377-382.	1.1	1
201	Development of dynamic aurora pulsed laser deposition equipped with reflection high-energy electron diffraction and effects of magnetic fields on room-temperature epitaxial growth of NiO thin film. Journal of the Ceramic Society of Japan, 2021, 129, 343-347.	1.1	1
202	Effects of Pressure on PbTiO ₃ Thin Film Prepared by Low-Pressure Thermal Plasma Deposition. Nippon Kinzoku Gakkaishi/Journal of the Japan Institute of Metals, 1999, 63, 62-67.	0.4	1
203	Low-temperature Synthesis of Functional Oxide Nanopowders by Sol-Gel method from Molecular-designed Metal Alkoxides. Journal of the Society of Powder Technology, Japan, 2012, 49, 378-389.	0.1	1
204	Cross Sectional Processing of Ferroelectric Thin Films by Ion-milling for AFM Analysis. Materia Japan, 2018, 57, 602-602.	0.1	1
205	Epitaxial growth of neodymia stabilized zirconia on Si(001) substrate using dynamic aurora PLD. Journal of the Ceramic Society of Japan, 2020, 128, 693-699.	1.1	1
206	Wide range lattice parameter control by aliovalent substitution to the rare-earth site in cubic garnet Li _{6.75} (La _{1â^'} <i>_x</i> Sm <i>_x3Zr_{1.7 Journal of the Ceramic Society of Japan, 2020, 128, 700-705.}</i>	′5< /su b>Ta	a _{0.25<!--</td-->}
207	Growth Mechanism and Effect of Deposition Rate on Crystal Orientation in PbTiO3 Thin Film by Metallorganic Chemical Vapor Deposition Journal of the Ceramic Society of Japan, 1999, 107, 955-960.	1.3	0
208	Effects of Oxygen Partial Pressure and Laser Energy Density on the Heteroepitaxial Growth of YSZ on Si(001) by Pulsed Laser Deposition Journal of the Ceramic Society of Japan, 2000, 108, 777-779.	1.3	0
209	Effect of Ti Source on Preparation of Pb-Based Oxide Thin Films Using LSCVD. Key Engineering Materials, 2001, 214-215, 129-132.	0.4	0
210	SiO _x Formation Process between YSZ and Si Substrate in YSZ/Si Thin Films by In-Situ TEM Analysis. Key Engineering Materials, 2002, 216, 153-0.	0.4	0
211	Effects of Deposition Temperature on Structure and Resistivity of Epitaxial La _{0.5} Sr _{0.5} CoO ₃ /CeO ₂ /YSZ/Si(001) Films. Key Engineering Materials, 2001, 214-215, 177-182.	0.4	0
212	Ferroelectric and Dielectric Properties of (Bi,La) ₄ Ti ₃ O ₁₂ /Pb(Zr,Ti)O ₃ Multilayer Thin Films on LaNiO ₃ -Coated Pt/Ti/SiO ₂ /Si Substrates. Key Engineering Materials, 2002, 228-229, 81-86.	0.4	0
213	Special Issue Ceramics Integration. Influence of Residual Stress on Structural and Dielectric Properties of Pb(Mg1/3Nb2/3)O3/BaTiO3/Pt/Ti/SiO2/Si Multi-Layered Thin Films Journal of the Ceramic Society of Japan, 2002, 110, 455-459.	1.3	0
214	Improvement of capacitance-voltage (C-V) characteristics of YSZ/Si(001) and ZrO2/Si thin film by Nb-doping. Materials Research Society Symposia Proceedings, 2002, 745, 911/T7.1.1.	0.1	0
215	Hrtem Investigation of Effect of Various Rare Earth Oxide Dopants on Epitaxial Zirconia High-K Gate Dielectrics. Materials Research Society Symposia Proceedings, 2002, 745, 971/T7.7.1.	0.1	0
216	Epitaxial Growth and Magnetic Behavior of (Ni,Zn)Fe2O4 Thin Films on Si Substrate Using Designed Buffer Layers for Novel Memory Application. Materials Research Society Symposia Proceedings, 2002, 747, 1.	0.1	0

#	Article	IF	CITATIONS
217	Improvement of capacitance-voltage (C-V) characteristics of YSZ/Si(001) and ZrO2/Si thin film by Nb-doping. Materials Research Society Symposia Proceedings, 2002, 747, 1.	0.1	Ο
218	Hrtem Investigation of Effect of Various Rare Earth Oxide Dopants on Epitaxial Zirconia High-k Gate Dielectrics. Materials Research Society Symposia Proceedings, 2002, 747, 1.	0.1	0
219	Ferroelectric and Dielectric Properties of Chemical-Solution-Derived Bismuth Lanthanum Titanate Thin Films with Various Bismuth Oxide Template layers. Materials Research Society Symposia Proceedings, 2002, 748, 1.	0.1	Ο
220	Special Issue Ceramics Integration. Comparative Study of Electrical Properties of Several(Bi,La)4Ti3O12/Pb(Zr,Ti)O3 Composite Thin Films Prepared by a Chemical Solution Deposition Method Journal of the Ceramic Society of Japan, 2002, 110, 460-464.	1.3	0
221	Preparation and Semiconducting Properties of Nb-Doped-SrTiO ₃ Thin Films having Controlled Crystal Orientation by MOCVD. Key Engineering Materials, 2003, 248, 111-116.	0.4	Ο
222	Effect of Remanent Magnetization of Ferromagnetic Thin Film on I-V Characteristics of MOS Transistor: I-V Characteristics by Epitaxial (Mn, Zn)Fe ₂ O ₄ Thin Film on Gate Area. Key Engineering Materials, 2003, 248, 165-168.	0.4	0
223	Effect of Remanent Magnetization of Ferromagnetic Thin Film on I-V Characteristics of MOS Transistor : I-V Characteristics of Circular and Opposite Patterned Ferromagnetic Thin Film Across Gate Area. Key Engineering Materials, 2003, 248, 173-178.	0.4	Ο
224	Structural and Electrical Properties of (Bi,La) ₄ Ti ₃ O ₁₂ Thin Films with a Bi ₂ O ₃ Top-Layer Prepared by a Chemical Solution Deposition Method. Key Engineering Materials, 2003, 248, 45-48.	0.4	0
225	In-Situ Magnetic Field Induced Structure and Properties of Epitaxial Spinel Ferrite Thin Films Prepared by Pulsed Laser Deposition (PLD) (Dynamic Aurora PLD Method). Materials Research Society Symposia Proceedings, 2004, 853, 63.	0.1	Ο
226	The Effect of Nb Doping to Control the Oxygen Defect and Improve C-V Properties of PLD Prepared YSZ Thin Film. Key Engineering Materials, 2004, 269, 233-236.	0.4	0
227	Atomic-Scale Structure Investigation of CeO ₂ /YSZ/Si Hetero-Interface by High Resolution Analytical Electron Microscope. Bunseki Kagaku, 2006, 55, 419-426.	0.2	Ο
228	Diffusion Behavior at the Interface of (Ba,Sr)TiO ₃ (BST)/Electrode/Buffer Layer/Si Epitaxial Multi-Layer Thin Film. Key Engineering Materials, 2006, 301, 257-260.	0.4	0
229	Investigation of Domain Structure and Electrical Properties of Monoclinic Epitaxial Zirconia Buffer Layer. Key Engineering Materials, 2006, 301, 261-264.	0.4	Ο
230	Ferroelectricity of BiFeO ₃ Thin Films by Pulsed Laser Deposition and Effect of Atmosphere. Key Engineering Materials, 2006, 320, 45-48.	0.4	0
231	Role of SrTiO3 Seed Layer on Low-temperature Crystallization of Pb(Zr, Ti)O3 Films Prepared by Metalorganic Chemical Vapor Deposition. Materials Research Society Symposia Proceedings, 2007, 1034, 7.	0.1	Ο
232	Fabrication and Optical Properties of Pb(Mg <inf>1/3</inf> Nb <inf>2/3</inf>)O <inf>3</inf> -PbTiO <inf>3</inf> Thin Films on Si Substrates by PLD Method. Applications of Ferroelectrics, IEEE International Symposium on, 2007, , .	0.0	0
233	Preparation of AlN thin films by means of CVD using iodide source under atmospheric pressure. Materials Research Society Symposia Proceedings, 2007, 1040, 1.	0.1	Ο
234	Preparation of InN by Means of AP-HCVD Using In Buffer Layers. Materials Research Society Symposia Proceedings, 2007, 1040, 1.	0.1	0

#	Article	IF	CITATIONS
235	Fabrication of HfO ₂ Thin Film on Si Substrate by Double-Pulse Excitation PLD. Key Engineering Materials, 2007, 350, 129-132.	0.4	0
236	Preparation of Epitaxial Pt Bottom Electrode and Tunability of (Ba,Sr)TiO ₃ Thin Film Deposited on Si Substrate. Ferroelectrics, 2008, 370, 132-139.	0.6	0
237	Polarized Raman Study in Pb(Zn1/3Nb2/3)O3-PbTiO3Mixed Crystal. Ferroelectrics, 2008, 376, 74-80.	0.6	Ο
238	Ferroelectric Properties of Epitaxial BiFe _{0.9} 7Mn _{0.03} O ₃ Thin Films with Different Crystal Orientations Deposited on Buffered Si Substrates. Key Engineering Materials, 2009, 421-422, 111-114.	0.4	0
239	Transition Layer in ZrO2 Ultra-Thin Film by Aberration-corrected TEM. Materia Japan, 2009, 48, 599-599.	0.1	Ο
240	Effect of Back-Etching on Electrical Properties of (111) - oriented PZT thin films. Transactions of the Materials Research Society of Japan, 2009, 34, 113-116.	0.2	0
241	Milling Effect of Calcium Aluminate Fine Particle Prepared by Chemical Solution Processing. Journal of the Society of Powder Technology, Japan, 2010, 47, 304-309.	0.1	Ο
242	Comparison of Thermal Stability of Epitaxially Grown (La _{0.5} Sr _{0.5})CoO ₃ and (La _{0.6} Sr _{0.4})MnO ₃ Thin Films Deposited on Si Substrate. Key Engineering Materials, 2010, 445, 160-163.	0.4	0
243	Preparation of heteroepitaxial SrRuO3 thin film on Si substrate and microstructure of BaTiO3-NiFe2O4 epitaxial composite thin film deposited on the SrRuO3 bottom electrode using PLD. Materials Research Society Symposia Proceedings, 2011, 1308, 71201.	0.1	Ο
244	TEM Study for Self-Orientated LaNiO ₃ Film along [100]. Key Engineering Materials, 0, 582, 185-188.	0.4	0
245	Effects of Oxide Seeding Layers on Electrical Properties of Chemical Solution Deposition-Derived Pb(Mg1/3Nb2/3)O3–PbTiO3Relaxor Thin Films. Japanese Journal of Applied Physics, 2013, 52, 09KA07.	1.5	Ο
246	Stress state analysis of stress engineered BaTiO ₃ thin film by LaNiO ₃ bottom electrode. Journal of the Ceramic Society of Japan, 2013, 121, 273-277.	1.1	0
247	Effect of facing annealing on crystallization and decomposition of Pb(Mg _{1/3} Nb _{2/3})O ₃ thin films prepared by CSD technique using MOD solution. Journal of the Ceramic Society of Japan, 2013, 121, 326-326.	1.1	Ο
248	Synthesis of Silica-Coated Magnetic Nanoparticles Using Acid Catalysis. Hosokawa Powder Technology Foundation ANNUAL REPORT, 2017, 25, 132-137.	0.0	0
249	Influence of Particle Size on the Spin Pinning Effect in the fcc-FePt Nanoparticles. Journal of Superconductivity and Novel Magnetism, 2019, 32, 1501-1505.	1.8	Ο
250	High-resolution TEM Analysis of ZrO ₂ Gate Dielectrics Co-doped with Y ₂ O ₃ Ta ₂ O ₅ . Materia Japan, 2006, 45, 841-841.	0.1	0
251	The effect of SrTiO3 seed and application of in-situ magnetic field on the preparation of Pb(Zr, Ti)O3 thin film by pulsed laser deposition. Transactions of the Materials Research Society of Japan, 2007, 32, 99-104.	0.2	0
252	Preparation of flat cross section of thin films by perforation fracture method. Journal of the Ceramic Society of Japan, 2020, 128, 706-709.	1.1	0